

LM614 Quad Operational Amplifier and Adjustable Reference

Check for Samples: LM614

FEATURES

Op Amp

Low Operating Current: 450µA

Wide Supply Voltage Range: 4V to 36V

Wide Common-Mode Range: V ⁻ to (V⁺− 1.8V)

 Wide Differential Input Voltage: ±36V Reference

Adjustable Output Voltage: 1.2V to 5.0V

Initial Tolerance: ±2.0%

 Wide Operating Current Range: 17μA to 20mA

• Tolerant of Load Capacitance

APPLICATIONS

- Transducer Bridge Driver and Signal Processing
- Process and Mass Flow Control Systems
- Power Supply Voltage Monitor
- Buffered Voltage References for A/D's

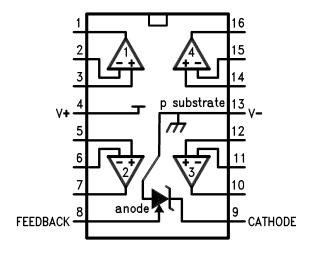
DESCRIPTION

The LM614 consists of four op-amps and a programmable voltage reference in a 16-pin package. The op-amp out-performs most single-supply opamps by providing higher speed and bandwidth along with low supply current. This device was specifically designed to lower cost and board space requirements in transducer, test, measurement and data acquisition systems.

Combining a stable voltage reference with four wide output swing op-amps makes the LM614 ideal for single supply transducers, signal conditioning and bridge driving where large common-mode-signals are common. The voltage reference consists of a reliable band-gap design that maintains low dynamic output impedance (1 Ω typical), initial tolerance (2.0%), and the ability to be programmed from 1.2V to 5.0V via two external resistors. The voltage reference is very stable even when driving large capacitive loads, as are commonly encountered in CMOS data acquisition systems.

As a member of TI's new Super-Block™ family, the LM614 is a space-saving monolithic alternative to a multichip solution, offering a high level of integration without sacrificing performance.

Connection Diagram



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings (1)(2)

Voltage on Any Pins except V _F (referred to V ⁻ pin)	36V (Max) ⁽³⁾ -0.3V (Min) ⁽⁴⁾						
Current through Any Input Pin	±20						
Differential Input Voltage	LM614I	LM614I					
	LM614C	LM614C					
Storage Temperature Range	-65°C ≤ T _J ≤ +150°C						
Maximum Junction Temperatu	150°C						
Thermal Resistance, Junction-	150°C						
Soldering Information (Soldering	220°C						
ESD Tolerance ⁽⁶⁾	±1kV						

- (1) Absolute maximum ratings indicate limits beyond which damage to the component may occur. Electrical specifications do not apply when operating the device beyond its rated operating conditions.
- (2) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.
- (3) Input voltage above V+ is allowed.
- (4) More accurately, it is excessive current flow, with resulting excess heating, that limits the voltages on all pins. When any pin is pulled a diode drop below V-, a parasitic NPN transistor turns ON. No latch-up will occur as long as the current through that pin remains below the Maximum Rating. Operation is undefined and unpredictable when any parasitic diode or transistor is conducting.
- (5) Junction temperature may be calculated using TJ = TA + P DθjA. The given thermal resistance is worst-case for packages in sockets in still air. For packages soldered to copper-clad board with dissipation from one comparator or reference output transistor, nominal θjA is 90°C/W for the DW package.
- (6) Human body model, 100 pF discharged through a 1.5 k Ω resistor.

Operating Temperature Range

LM614I	-40°C ≤ T _J ≤ +85°C
LM614C	0°C ≤ T _J ≤ +70°C

Electrical Characteristics

These specifications apply for $V^- = GND = 0V$, $V^+ = 5V$, $V_{CM} = V_{OUT} = 2.5V$, $I_R = 100\mu A$, FEEDBACK pin shorted to GND, unless otherwise specified. Limits in standard typeface are for $T_J = 25$ °C; limits in **Boldface type** apply over the **Operating Temperature Range**.

Symbol	Parameter	Conditions	Typ ⁽¹⁾	LM614I LM614C Limits ⁽²⁾	Units
I _S	Total Supply Current	$R_{LOAD} = \infty$, 4V \leq V^+ \leq 36V (32V for LM614C)	450 550	1000 1070	μΑ max μΑ max
V _S	Supply Voltage Range		2.2 2.9	2.8 3	V min V min
			46 43	32 32	V max V max
OPERATIONAL	AMPLIFIER			•	•
V _{OS1}	V _{OS} Over Supply	$4V \le V^+ \le 36V$ ($4V \le V^+ \le 32V$ for LM614C)	1.5 2.0	5.0 7.0	mV max mV max
V _{OS2}	V _{OS} Over V _{CM}	$V_{CM} = 0V \text{ through } V_{CM} = (V^+ - 1.8V), V^+ = 30V$	1.0 1.5	5.0 7.0	mV max mV max
<u>V_O</u> S3 ΔT	Average V _{OS} Drift	See ⁽²⁾	15		μV/°C max
I _B	Input Bias Current		10 11	35 40	nA max nA max
Ios	Input Offset Current		0.2 0.3	4 5	nA max nA max

- (1) Typical values in standard typeface are for TJ = 25°C; values in boldface type apply for the full operating temperature range. These values represent the most likely parametric norm.
- (2) All limits are ensured at room temperature (standard type face) or at operating temperature extremes (bold type face).

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Electrical Characteristics (continued)

These specifications apply for $V^- = GND = 0V$, $V^+ = 5V$, $V_{CM} = V_{OUT} = 2.5V$, $I_R = 100\mu A$, FEEDBACK pin shorted to GND, unless otherwise specified. Limits in standard typeface are for $T_J = 25$ °C; limits in **Boldface type** apply over the **Operating Temperature Range**.

Symbol	Parameter	Conditions	Typ ⁽¹⁾	LM614I LM614C Limits ⁽²⁾	Units
l _{OS1} ΔT	Average Offset Drift Current		4		pA/°C
R _{IN}	Input Resistance	Differential	1800		ΜΩ
		Common-Mode	3800		ΜΩ
C _{IN}	Input Capacitance	Common-Mode Input	5.7		pF
e _n	Voltage Noise	f = 100 Hz, Input Referred	74		nV/√ Hz
I _n	Current Noise	f = 100 Hz, Input Referred	58		fA/√ Hz
CMRR	Common-Mode	$V^{+} = 30V, 0V \le V_{CM} \le (V^{+} - 1.8V),$	95	75	dB min
	Rejection Ratio	CMRR = 20 log ($\Delta V_{CM}/\Delta V_{OS}$)	90	70	dB min
PSRR	Power Supply	$4V \le V^+ \le 30V$, $V_{CM} = V^+/2$,	110	75	dB min
	Rejection Ratio	$PSRR = 20 \log (\Delta V^{+}/\Delta V_{OS})$	100	70	dB min
A _V	Open Loop Voltage Gain	R _L = 10 k Ω to GND, V ⁺ = 30V, 5V \leq V _{OUT} \leq 25V	500 50	94 40	V/mV min
SR	Slew Rate	V + = 30V ⁽³⁾	±0.70 ±0.65	±0.50 ± 0.45	V/µs
GBW	Gain Bandwidth	C _L = 50 pF	0.8 0.52		MHz MHz
V _{O1}	Output Voltage Swing High	R _L = 10 kΩ to GND V + = 36V (32V for LM614C)	V ⁺ - 1.4 V ⁺ - 1.6	V ⁺ - 1.8 V⁺ - 1.9	V min V min
V _{O2}	Output Voltage Swing Low	R _L = 10 kΩ to V ⁺ V ⁺ = 36V (32V for LM614C)	V - + 0.8 V- + 0.9	V ⁻ + 0.95 V ⁻ + 1.0	V max V max
I _{OUT}	Output Source	$V_{OUT} = 2.5V, V_{+IN} = 0V, V_{-IN} = -0.3V$	25 15	16 13	mA min mA min
I _{SINK}	Output Sink Current	$V_{OUT} = 1.6V, V_{+IN} = 0V, V_{-IN} = 0.3V$	17 9	13 8	mA min mA min
I _{SHORT}	Short Circuit Current	V _{OUT} = 0V, V _{+IN} = 3V, V _{-IN} = 2V, Source	30 40	50 60	mA max mA max
		$V_{OUT} = 5V, V_{+IN} = 2V, V_{-IN} = 3V, Sink$	30 32	70 90	mA max mA max
VOLTAGE REF	ERENCE				
V_{R}	Voltage Reference	See ⁽⁴⁾	1.244	1.2191 1.2689 (±2.0%)	V min V max
<u>ΔV</u> _R ΔT	Average Temperature Drift	See (5)	10	150	PPM/°C max
<u>ΔV</u> _R ΔT _J	Hysteresis	See (6)	3.2		μV/°C
ΔV_R	V _R Change with Current	V _{R(100 μA)} – V _{R(17 μA)}	0.05 0.1	1 1.1	mV max mV max
ΔI _R		V _{R(10 mA)} - V _{R(100 μA)} (7)	1.5 2.0	5 5.5	mV max mV max

⁽³⁾ Slew rate is measured with op amp in a voltage follower configuration. For rising slew rate, the input voltage is driven from 5V to 25V, and the output voltage transition is sampled at 10V and @20V. For falling slew rate, the input voltage is driven from 25V to 5V, and the output voltage transition is sampled at 20V and 10V.

⁽⁴⁾ V_R is the Cathode-feedback voltage, nominally 1.244V.

⁽⁵⁾ Average reference drift is calculated from the measurement of the reference voltage at 25°C and at the temperature extremes. The drift, in ppm/°C, is 10⁶•ΔV _R/(V_{R[25°C]}•ΔT_J), where ΔV _R is the lowest value subtracted from the highest, V_{R[25°C]} is the value at 25°C, and ΔT_J is the temperature range. This parameter is ensured by design and sample testing.

⁽⁶⁾ Hysteresis is the change in V_R caused by a change in T_J, after the reference has been "dehysterized". To dehysterize the reference; that is minimize the hysteresis to the typical value, cycle its junction temperature in the following pattern, spiraling in toward 25°C; 25°C, 85°C, −40°C, 70°C, 0°C, 25°C.

⁽⁷⁾ Low contact resistance is required for accurate measurement.



Electrical Characteristics (continued)

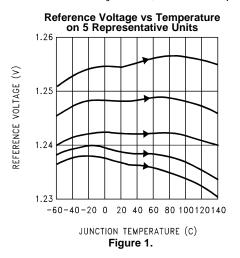
These specifications apply for $V^- = GND = 0V$, $V^+ = 5V$, $V_{CM} = V_{OUT} = 2.5V$, $I_R = 100\mu A$, FEEDBACK pin shorted to GND, unless otherwise specified. Limits in standard typeface are for $T_J = 25$ °C; limits in **Boldface type** apply over the **Operating Temperature Range**.

Symbol	Parameter	Conditions	Typ ⁽¹⁾	LM614I LM614C Limits ⁽²⁾	Units
R	Resistance	ΔV _{R(10→0.1 mA)} /9.9 mA ΔV _{R(100→17 μA)} /83 μA	0.2 0.6	0.56 13	Ω max Ω max
$\frac{\Delta V_{R}}{AV_{RO}}$	V _R Change with High V _{RO}	V _{R(Vro = Vr)} - V _{R(Vro = 5.0V)} (3.76V between Anode and FEEDBACK)	2.5 2.8	7 10	mV max mV max
ΔV_{R}	V _R Change with V ⁺ Change	V _{R(V + = 5V)} - V _{R(V + = 36V)} (V ⁺ = 32V for LM614C)	0.1 0.1	1.2 1.3	mV max mV max
$\frac{\Delta V_R}{\Delta V}$		$V_{R(V +=5V)} - V_{R(V +=3V)}$	0.01 0.01	1 1.5	mV max mV max
I _{FB}	FEEDBACK Bias Current	V _{ANODE} ≤ V _{FB} ≤ 5.06V	22 29	50 55	nA max nA max
e _n	Voltage Noise	BW = 10 Hz to 10 kHz, $V_{RO} = V_R$	30		μV _{RMS}

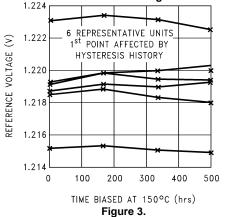


Typical Performance Characteristics (Reference)

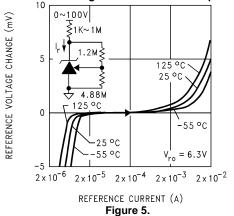
 $T_J = 25$ °C, FEEDBACK pin shorted to $V^- = 0V$, unless otherwise noted



Accelerated Reference Voltage Drift vs. Time



Reference Voltage vs. Current and Temperature



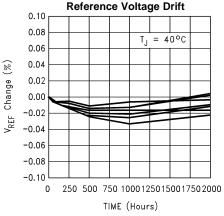
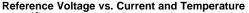
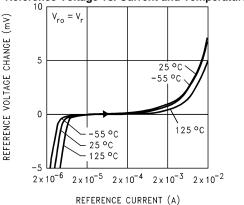


Figure 2.





Reference Voltage vs. Reference Current

Figure 4.

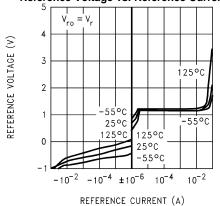


Figure 6.



Typical Performance Characteristics (Reference) (continued)

 $T_J = 25$ °C, FEEDBACK pin shorted to $V^- = 0$ V, unless otherwise noted

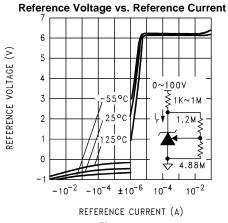


Figure 7.

FEEDBACK Current vs. FEEDBACK-to-Anode Voltage

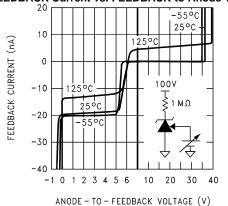
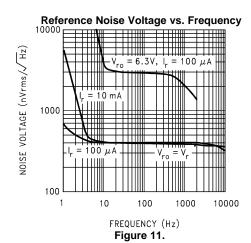


Figure 9.



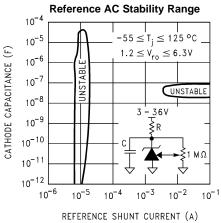


Figure 8.

FEEDBACK Current vs. FEEDBACK-to-Anode Voltage

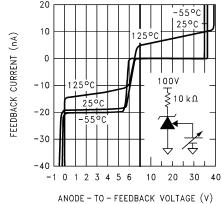


Figure 10.

Reference Small-Signal Resistance vs. Frequency

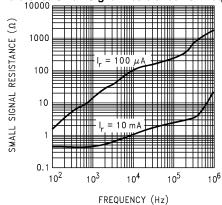


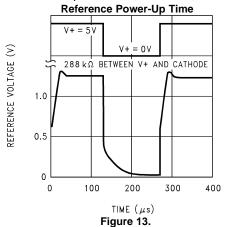
Figure 12.

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Typical Performance Characteristics (Reference) (continued)

 $T_J = 25$ °C, FEEDBACK pin shorted to $V^- = 0V$, unless otherwise noted



Reference Voltage with FEEDBACK Voltage Step

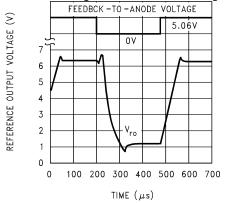


Figure 14.

Reference Voltage with 100~12 µA Current Step

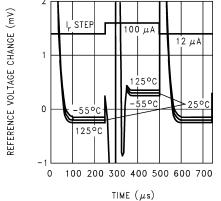
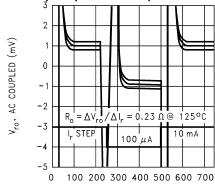


Figure 15.

Reference Step Response for 100 $\mu A \sim 10$ mA Current Step



TIME (μs) Figure 16.

Reference Voltage Change with Supply Voltage Step

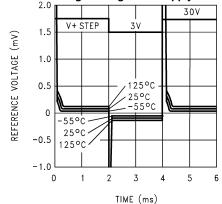


Figure 17.



Typical Performance Characteristics (Op Amps)

 $V^+ = 5V$, $V^- = GND = 0V$, $V_{CM} = V^+/2$, $V_{OUT} = V^+/2$, $T_J = 25^{\circ}C$, unless otherwise noted

Input Common-Mode Voltage Range vs. Temperature

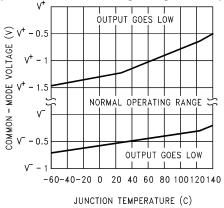
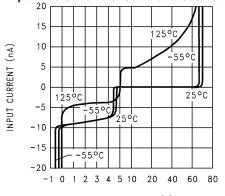
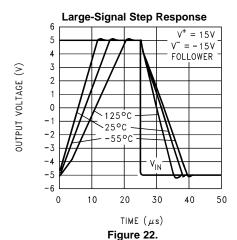


Figure 18.

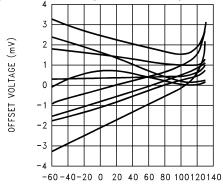
Input Bias Current vs. Common-Mode Voltage



INPUT VOLTAGE (V) Figure 20.

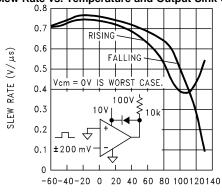


V_{OS} vs. Junction Temperature on 9 Representative Units



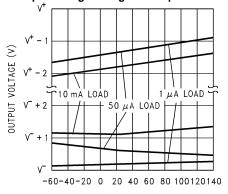
JUNCTION TEMPERATURE (C) Figure 19.

Slew Rate vs. Temperature and Output Sink Current



JUNCTION TEMPERATURE (C) Figure 21.

Output Voltage Swing vs. Temp. and Current



JUNCTION TEMPERATURE (C)

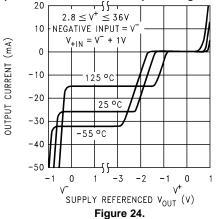
Figure 23.

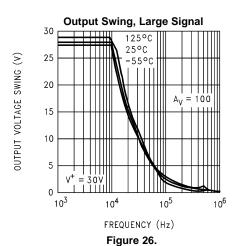


Typical Performance Characteristics (Op Amps) (continued)

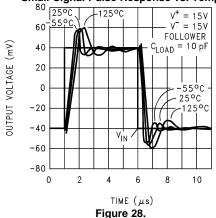
 $V^+ = 5V, \ V^- = GND = 0V, \ V_{CM} = V^+/2, \ V_{OUT} = V^+/2, \ T_J = 25^{\circ}C, \ unless \ otherwise \ noted$ Output Source Current vs. Output Voltage and Temp. Output Sink











Output Sink Current vs. Output Voltage and Temp.

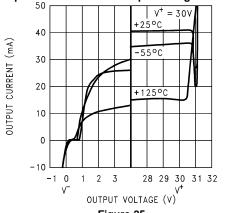


Figure 25.

Output Impedance vs. Frequency and Gain

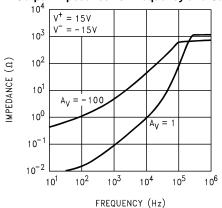


Figure 27.

Small-Signal Pulse Response vs. Load

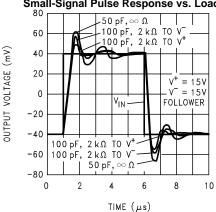
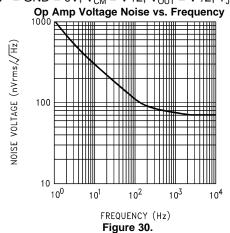


Figure 29.

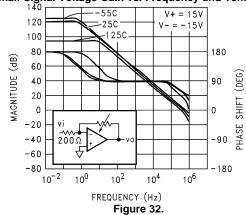


Typical Performance Characteristics (Op Amps) (continued)

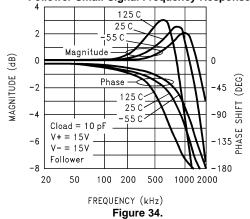
 $V^+ = 5V$, $V^- = GND = 0V$, $V_{CM} = V^+/2$, $V_{OUT} = V^+/2$, $T_J = 25$ °C, unless otherwise noted



Small-Signal Voltage Gain vs. Frequency and Temperature



Follower Small-Signal Frequency Response



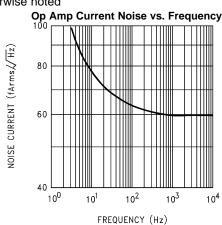
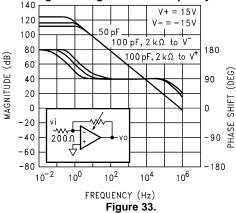


Figure 31.

Small-Signal Voltage Gain vs. Frequency and Load



Common-Mode Input Voltage Rejection Ratio

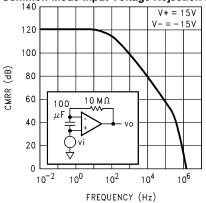
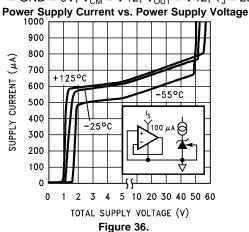


Figure 35.

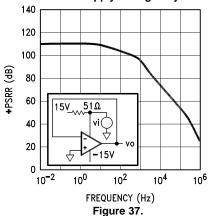


Typical Performance Characteristics (Op Amps) (continued)

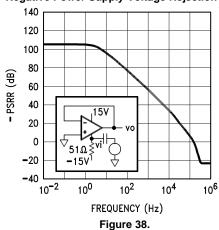
 $V^+ = 5V$, $V^- = GND = 0V$, $V_{CM} = V^+/2$, $V_{OUT} = V^+/2$, $T_J = 25$ °C, unless otherwise noted



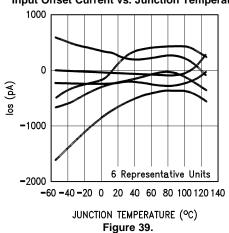
Positive Power Supply Voltage Rejection Ratio



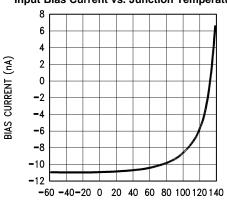
Negative Power Supply Voltage Rejection Ratio



Input Offset Current vs. Junction Temperature



Input Bias Current vs. Junction Temperature

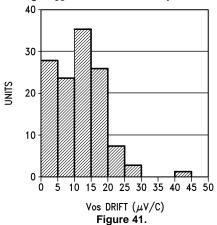


JUNCTION TEMPERATURE (°C) Figure 40.

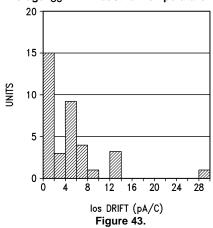


Typical Performance Distributions

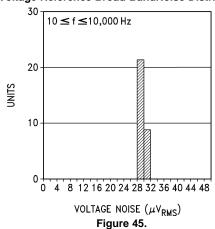
Average V_{OS} Drift Industrial Temperature Range



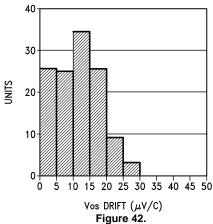
Average I_{OS} Drift Industrial Temperature Range



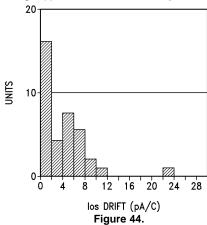
Voltage Reference Broad-BandNoise Distribution



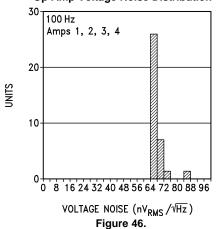
Average V_{OS} Drift Commercial Temperature Range



Average I_{OS} Drift Commercial Temperature Range

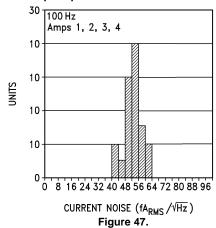


Op Amp Voltage Noise Distribution





Typical Performance Distributions (continued) Op Amp Current Noise Distribution





APPLICATION INFORMATION

VOLTAGE REFERENCE

Reference Biasing

The voltage reference is of a shunt regulator topology that models as a simple zener diode. With current I_r flowing in the "forward" direction there is the familiar diode transfer function. I_r flowing in the reverse direction forces the reference voltage to be developed from cathode to anode. The cathode may swing from a diode drop below V^- to the reference voltage or to the avalanche voltage of the parallel protection diode, nominally 7V. A 5.0V reference with V^+ = 3V is allowed.

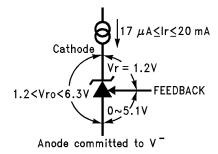


Figure 48. Voltages Associated with Reference (Current Source I_r is External)

The reference equivalent circuit reveals how V_r is held at the constant 1.2V by feedback, and how the FEEDBACK pin passes little current.

To generate the required reverse current, typically a resistor is connected from a supply voltage higher than the reference voltage. Varying that voltage, and so varying I_r, has small effect with the equivalent series resistance of less than an ohm at the higher currents. Alternatively, an active current source, such as the LM134 series, may generate I_r.

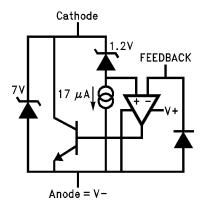


Figure 49. Reference Equivalent Circuit

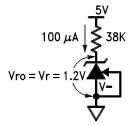


Figure 50. 1.2V Reference

Product Folder Links: *LM614*



Capacitors in parallel with the reference are allowed. See Reference AC Stability Range typical curve for capacitance values—from 20 μ A to 3 mA any capacitor value is stable. With the reference's wide stability range with resistive and capacitive loads, a wide range of RC filter values will perform noise filtering.

Adjustable Reference

The FEEDBACK pin allows the reference output voltage, V_{ro} , to vary from 1.24V to 5.0V. The reference attempts to hold V_r at 1.24V. If V_r is above 1.24V, the reference will conduct current from Cathode to Anode; FEEDBACK current always remains low. If FEEDBACK is connected to Anode, then $V_{ro} = V_r = 1.24V$. For higher voltages FEEDBACK is held at a constant voltage above Anode—say 3.76V for $V_{ro} = 5V$. Connecting a resistor across the constant V_r generates a current $I=V_r/R1$ flowing from Cathode into FEEDBACK node. A Thevenin equivalent 3.76V is generated from FEEDBACK to Anode with R2=3.76/I. For a 1% error, use R1 such that I is greater than one hundred times the FEEDBACK bias current. For example, keep I $\geq 5.5\mu$ A.

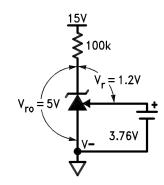
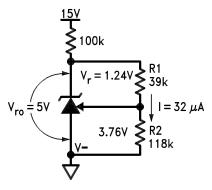


Figure 51. Thevenin Equivalent of Reference with 5V Output



 $\begin{array}{l} R1 = Vr/I = 1.24/32 \mu = 39k \\ R2 = R1 \; \{(Vro/Vr) - 1\} = 39k \; \{(5/1.24) - 1)\} = 118k \end{array}$

Figure 52. Resistors R1 and R2 Program Reference Output Voltage to be 5V

Understanding that V_r is fixed and that voltage sources, resistors, and capacitors may be tied to the FEEDBACK pin, a range of V_r temperature coefficients may be synthesized.



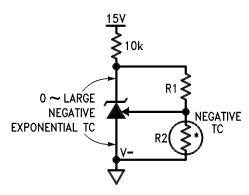


Figure 53. Output Voltage has Negative Temperature Coefficient (TC) if R2 has Negative TC

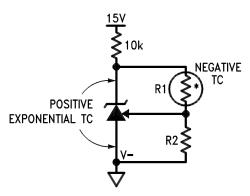


Figure 54. Output Voltage has Positive TC if R1 has Negative TC

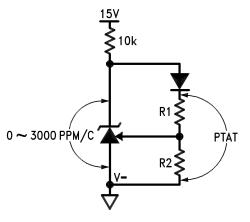
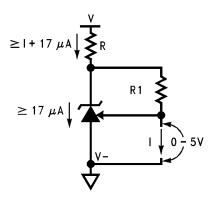


Figure 55. Diode in Series with R1 Causes Voltage across R1 and R2 to be Proportional to Absolute Temperature (PTAT)

Connecting a resistor across Cathode-to-FEEDBACK creates a 0 TC current source, but a range of TCs may be synthesized.





I = Vr/R1 = 1.24/R1

Figure 56. Current Source is Programmed by R1

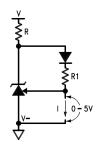


Figure 57. Proportional-to-Absolute-Temperature Current Source

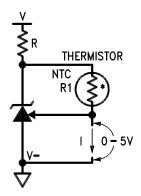


Figure 58. Negative-TC Current Source

Hysteresis

The reference voltage depends, slightly, on the thermal history of the die. Competitive micro-power products vary—always check the data sheet for any given device. Do not assume that no specification means no hysteresis.



OPERATIONAL AMPLIFIERS

Any amp or the reference may be biased in any way with no effect on the other amps or reference, except when a substrate diode conducts (see Electrical Characteristics). One amp input may be outside the common-mode range, another amp may be operated as a comparator, another with all terminals floating with no effect on the others (tying inverting input to output and non-inverting input to V⁻ on unused amps is preferred). Choosing operating points that cause oscillation, such as driving too large a capacitive load, is best avoided.

Op Amp Output Stage

These op amps, like their LM124 series, have flexible and relatively wide-swing output stages. There are simple rules to optimize output swing, reduce cross-over distortion, and optimize capacitive drive capability:

- 1. Output Swing: Unloaded, the $42\mu A$ pull-down will bring the output within 300 mV of V⁻ over the military temperature range. If more than $42\mu A$ is required, a resistor from output to V⁻ will help. Swing across any load may be improved slightly if the load can be tied to V⁺, at the cost of poorer sinking open-loop voltage gain
- Cross-over Distortion: The LM614 has lower cross-over distortion (a 1 V_{BE} deadband versus 3 V_{BE} for the LM124), and increased slew rate as shown in the characteristic curves. A resistor pull-up or pull-down will force class-A operation with only the PNP or NPN output transistor conducting, eliminating cross-over distortion
- 3. Capacitive Drive: Limited by the output pole caused by the output resistance driving capacitive loads, a pull-down resistor conducting 1 mA or more reduces the output stage NPN r_e until the output resistance is that of the current limit 25 Ω . 200pF may then be driven without oscillation.

Op Amp Input Stage

The lateral PNP input transistors, unlike most op amps, have BV_{EBO} equal to the absolute maximum supply voltage. Also, they have no diode clamps to the positive supply nor across the inputs. These features make the inputs look like high impedances to input sources producing large differential and common-mode voltages.

Typical Applications

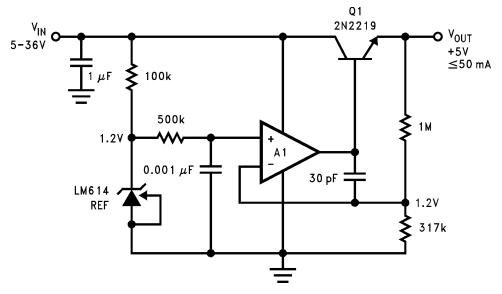
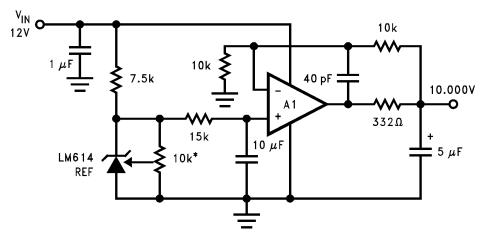


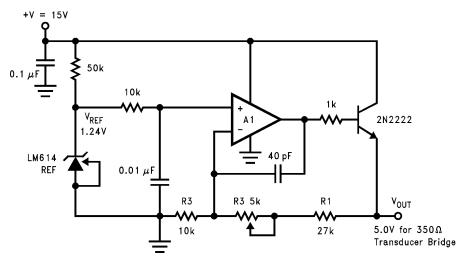
Figure 59. Simple Low Quiescent Drain Voltage Regulator. Total supply current approximately 320 μ A, when V_{IN} = +5V.





*10k must be low t.c. trimpot.

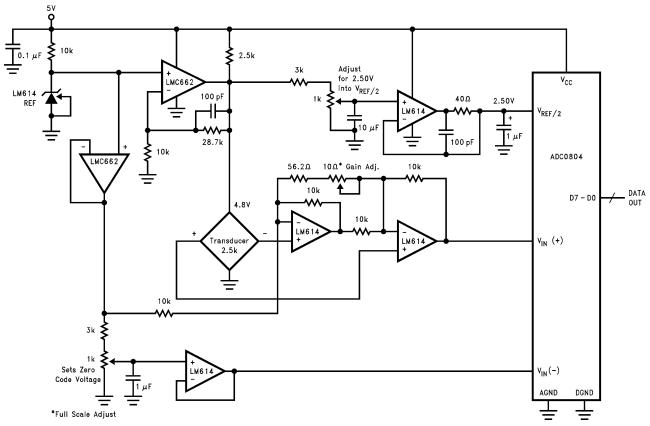
Figure 60. Ultra Low Noise 10.00V Reference. Total output noise is typically $14\mu V_{RMS}$.



 V_{OUT} = (R₁ /Pe + 1) V _{REF} R₁, R₂ should be 1% metal film P_{\beta} should be low T.C. trim pot

Figure 61. Slow Rise Time Upon Power-Up, Adjustable Transducer Bridge Driver.
Rise time is approximately 1ms.





(1) Set zero code voltage, then adjust 10Ω gain adjust pot for full scale.

Figure 62. Transducer Data Acquisition System.



Simplified Schematic Diagrams

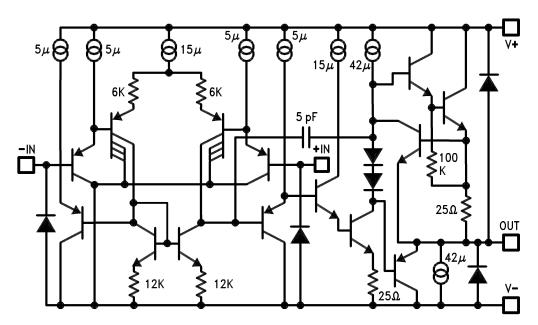


Figure 63. Op Amp

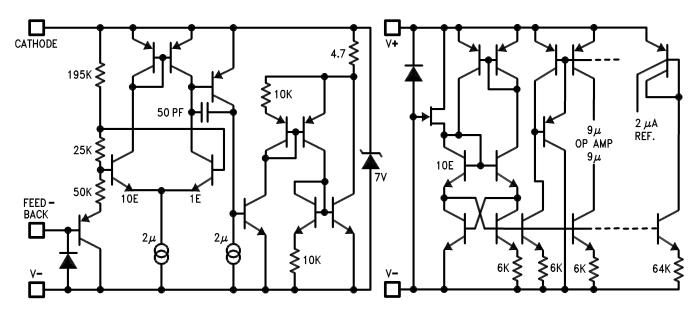


Figure 64. Reference / Bias



REVISION HISTORY

Cr	nanges from Revision B (March 2013) to Revision C	Page
•	Changed layout of National Data Sheet to TI format	21



PACKAGE OPTION ADDENDUM

24-Aug-2018

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
LM614 MDC	ACTIVE	DIESALE	Y	0	100	Green (RoHS & no Sb/Br)	Call TI	Level-1-NA-UNLIM	-40 to 85		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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